

MARKED-UP VERSION OF SUBSTITUTE SPECIFICATION

TITLE

An improved ~~tunable~~tunable delay line.

5 TECHNICAL FIELD

The present invention relates to a tunable electromagnetic delay line, comprising a first conductor with a first main direction of extension, said first conductor being arranged on top of a non-conducting substrate.

10 BACKGROUND ART

Delay lines are a common component in many contemporary electrical systems, usually microwave systems. Examples that could be mentioned of fields of technology where delay lines are used are radar systems, amplifiers and oscillators.

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Most technologies used in delay lines result in bulky components, which are usually not cost-effective and are difficult to integrate with standard semiconductor technologies. Moreover, it is quite desirable for a delay line to be ~~tunable~~tunable, i.e., to have a delay time which can be altered. In addition, most contemporary ~~tunable~~tunable delay lines are quite power consuming, which is usually a drawback.

DISCLOSURE OF THE INVENTION SUMMARY

Hence, as described above, there is a need for a ~~tunable~~tunable delay line which is of a small size, has low power consumption, and capable of having long delay times.

- 5 This need is met by the technology in this application. ~~present invention in that it discloses a~~A tunable electromagnetic delay line which comprises a first conductor with a first main direction of extension, ~~where the~~The first conductor is arranged on top of a non-conducting substrate.
- 10 The delay line ~~of the invention~~ additionally comprises a layer of a ferroelectric material with first and second main surfaces, which layer separates the first conductor and the substrate. The delay line also comprises a second conductor with a second main direction of extension.
- 15 The first and second main directions of extensions essentially coincide with each other, and the first and second conductors are each other's mirror image with respect to an ~~imagined~~imaginary line in the center of the delay line along ~~said~~the first and second main directions of extension. The tuning of the delay line ~~of the invention~~ is accomplished by applying a voltage between 20 ~~said~~ first and second conductors.

The advantages afforded by this design will become evident in the detailed description given below.

BRIEF DESCRIPTION OF THE DRAWINGS

The invention will be described in more detail in the following, with reference being made to the drawings, in which

5 Fig 1 shows a top view of a first non-limiting example embodiment of the invention, and

Fig 2 shows a cross section of the device of fig Fig 1, along the line II-II, and

Fig 3 shows a top view of a second non-limiting example embodiment, of the invention, and

Fig 4 shows a cross section of the device of fig Fig 3, along the line III-III, and

10 Fig Figs 5a, 5b, and 5c show shows a top view of another non-limiting example embodiment, of the invention, and

Fig 6 shows a cross section of the device of fig Fig 5, along the line VI- VI, and

15 Figs 7-12 show top views of various other non-limiting example embodiments of the invention.

EMBODIMENTS DETAILED DESCRIPTION

In fig 1, a first non-limiting example embodiment 100 of a tunable tunable delay line according to the invention is shown in top view. The delay line 100 comprises a first conductor 110, which has a first main direction of extension, indicated by the arrow A in fig 1. In addition to the first conductor 110, the delay line 100 also comprises a second conductor 120, which has a second main direction of extension, indicated by the arrow B in fig 1.

Shifting now to fig 2, a cross section of the arrangement 100 from fig 1 is shown, along the line II – II in fig 1. As can be seen in fig 2, the first and the second conductors 110, 120 are arranged on top of a layer 130 of a ferroelectric material which has a high permittivity. Some examples of such 5 materials are BaTiO_3 , SrTiO_3 and various combinations of Ba, Sr and TiO_3 , usually expressed as $\text{Ba}_x\text{Sr}_{(1-x)}\text{TiO}_3$ or combinations of Na, K and NO_3 , usually expressed as $\text{Na}_x\text{K}_{(1-x)}\text{NO}_3$.

Below the layer 130 of the ferroelectric material, there is arranged a 10 supporting layer or substrate 240 of a non-conducting material. In fig 2, there is also schematically shown how the delay τ of the device 100 is altered: an AC control voltage, V_{TUNE} , is applied between the first and second conductors 110, 120, and the voltage is altered to achieve the desired delay τ . Also indicated in fig 2 with broken lines, is the fact that there is a capacitive 15 coupling between the two conductors 110, 120.

Reverting Returning now to fig 1, it can be seen that in the delay line 100 of the invention, the first main direction of extension, A, of the first conductor 110 essentially coincides with the second main direction of extension, B, of 20 the second conductor 120, and also that the first 110 and second 120 conductors are each other's mirror image with respect to an imagined imaginary line C in the center of the delay line, along thesaid first and second main directions of extension.

Preferably, as can also be seen in fig 1, the first conductor 110 is meander shaped, and is comprised alternately of sections 111 with a second direction of extension, and sections 113 with a third direction of extension. The second conductor 120 is comprised alternately of sections 112 with a 5 fourth direction of extension and sections 115 with a fifth direction of extension.

According to the invention, the ~~The~~ second and fourth directions of extension essentially coincide with each other, and the third and fifth directions of 10 extension also essentially coincide with each other.

In the embodiment shown in fig 1, the second and third directions of extension of the first conductor are essentially perpendicular to each other, with the second direction of extension essentially coinciding with the first 15 conductors first main direction of extension. Due to the meander shape of the embodiment shown in fig 1, ~~what this means is that~~ both the first and the second conductor have one section that points "straight ahead", i.e., in a general direction of the device, and then one section that is perpendicular to the general direction of the device. Both conductors have alternating such 20 sections, which is what causes the meander shape of the conductors in this embodiment.

As mentioned previously, and as also shown in fig 2, there is a capacitive coupling between the two conductors of the device.

Another example embodiment 300 of the invention is shown in fig 3. This embodiment enables more flexibility in terms of tailoring the impedance of the device. The device 100 of figs 1 and 2 comprises inductors in the form of the

5 meander lines, but only has an implicit (?) capacitive coupling between the meander lines. The embodiment 300, as opposed to this, is equipped with includes capacitors, shown with dashed lines in fig 3, and in a cross section in fig 4, the cross section being along the line IV - IV in fig 3.

10 As shown in fig-figs 3 and 4, the embodiment 300 comprises the same meander shaped first 310 and second 320 conductors as the embodiment 100 in figs 1 and 2. However, the embodiment 300 additionally comprises a third conductor 350 (see Fig 4) arranged between the non-conducting substrate and the layer of ferroelectric material, with the third conductor being

15 arranged so that it extends from a point below the first conductor to a point below the second conductor, in a direction of extension which is essentially perpendicular to said first and second directions of extension.

Preferably, the third conductor 350 is arranged below the first 310 and

20 second 320 conductors at a point below sections of the first and second conductors that point in the general direction A/B (see Fig 3) of the device 300, the third conductor then being arranged so that it "connects" the first and second conductors, the word "connect" here being used in the sense that at least a first part of the third conductor is located below the first conductor,

and at least a second part of the third conductor is located below the second conductor. Thus, capacitors are formed between the first and second conductor respectively, and the third conductor.

5 Suitably, such third conductors are arranged at all or most of those locations on the device 300 which fulfill the conditions stated above for the location of the third conductor 350. Thus, the device 300 ~~of the invention will exhibit~~ includes a plurality of such conductors, all located at corresponding places in the device 300.

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Tuning of the delay of the delay line 300 is accomplished by applying a DC-voltage between the first 310 and the second 320 conductors, as shown in fig 4.

15 Yet a further example embodiment 500 of a device according to the invention is shown in figs 5a – 5c. This embodiment shows a way of decreasing the ohmic losses[:]. a A first conducting pattern, a first delay line 505, shown in fig 5c, is formed in the bottom layer of the device, i.e. between a substrate and a ferroelectric material, the first delay line 505 being essentially similar to 20 those shown in figs 1 and 3, i.e. it has two meander shaped conductors 510, 520, essentially parallel to each other, extending in a common general direction, whichwhere the conductors are essentially each other's mirror image with respect to an imagined imaginary line C between them, saidthe imagined line extending in the general direction of the device.

Thus, the two conductors of the delay line 505 have one section 532 that points "straight ahead", i.e. in the general direction of the device, and then one section 531 that is perpendicular to the general direction C of the device

5 500. Both conductors 510, 520, have alternating such sections, each section being joined to the next one. Thus, each conductor has a recurring pattern of two parallel sections 531, 534, that point "outwards" with respect to the general direction of the device, with thesaid two parallel sections being joined at the "outer" edge of the device by a conductor 532 which is perpendicular to

10 thesaid two parallel sections. Each of thesaid two parallel sections 531, 534, is then joined at its other end, the "inner end" of the meander pattern, to an adjoining such section by a conductor 533 which is again perpendicular to the direction of the parallel sections.

15 As shown in fig 6, which is a cross section of the device of fig 5-a-5a along the line VI-IV— VIIV, the device 500 also comprises a second conducting pattern, 510 arranged on top of the ferroelectric layer. The second conducting pattern 510 is shown in top view in fig 5b[::]. The second conducting pattern 510 is similar to the first conducting pattern 505, with the exception that it does not exhibit the joining conductors 533 at the "inner end".

In the device 500, the first and second conducting patterns are arranged so that corresponding sections "cover" each other, resulting in the device shown

in fig 5a. As can be seen in fig 5b, the second conducting pattern 510 also exhibits conducting strips 512 which "connect" the joining strips of at the "inner edge" of the first conducting pattern, i.e. the connecting strips 512 in the second conducting pattern extend in a direction perpendicular to the 5 general direction of the device, so as to cover or connect one connecting strip in each meander line of the first conducting pattern.

10 In The the delay lines shown in figs 1-4, 5a-5c, and 6, 1-5 and described
above have many positive qualities, but there is a certain amount of mutual
negative coupling between the inductor strips, i.e., the meander lines, which
will reduce reduces the total inductance of the device, and thus negatively,
influence influences the delay time of the devices.

15 Fig 7 shows an example embodiment 700 of the invention which will alleviate
alleviates the problem of mutual negative coupling between the strips [:] the
The device comprises a first conducting pattern 710 and a second 720
conducting pattern, arranged on different sides of the ferroelectric layer. Each
of the conducting patterns alternatingly comprises sections arranged at 45
degrees or negative 45 degrees, with respect to the general direction C of the
20 device. However, if the first section 721-712 of the first conductor is arranged
at 45 degrees, the first section 713 of the second conductor will be arranged
at negative 45 degrees, the two conductors being arranged so that sections
which point in different directions intersect each other. Due to the geometry

of this, the sections will intersect each other at an angle of 90 degrees, which will essentially eliminate the negative magnetic coupling between the strips.

In a more generalized sense, the embodiment shown in fig 7 could be

5 | described in the following way[:]. The first conductor 710 alternatingly comprises sections of a second direction of extension 712 and a third 711 direction of extension 711, with the second direction 712 of extension 712 being at an angle α with respect to the device's main direction C of extension and the third direction 713 of extension 713 being at an angle β with respect

10 | to the device's main direction C of extension, α being in the interval between zero and ninety degrees, and β being in the interval between ninety and one hundred eighty degrees.

15 | The second conductor 720 also comprises sections of a fourth direction of extension 713 and a fifth 714 direction of extension 714, with the fourth direction of extension being at an angle α' with respect to the device's main direction C of extension and the fifth direction of extension being at an angle β' with respect to the device's main direction C of extension, α' being in the interval between zero and minus ninety degrees, and β' being in the interval

20 | between minus ninety and minus one hundred eighty degrees.

| The first conductor 710 and second conductor 720 conductors are arranged in the delay line 700 so that the first conductor's sections 712 in the second direction of extension cross the second conductor's sections 713 in the fourth

direction of extension, and so that the first conductor's sections 711 in the third direction of extension cross the second conductor's sections in the fifth 714 direction of extension 714.

5 Fig 8 shows a version 800 of the device of fig 7. In this embodiment, the sections of the two strips 810, 820, do not intersect each other, rather, they will only coincide or "cover each other" in their respective layers at those points where two adjacent sections in each conductor are joined to each other. One such point 815 has been encircled in fig 8 for the 10 sake of clarity.

The embodiments versions of the invention which have been shown in figs 1-4, 5a-5c, 6-8, 1-8 and described above exhibit excellent properties with respect to wide-band applications. but fig Fig 9 shows a way of achieving 15 even better wide-band properties. the The basic design of fig 7 is adhered to, but the width of the device is tapered.

As an alternative to tapering the device as shown in fig 9, as shown in fig 10, the device can periodically taper and then widen again, in the same 20 dimension that it tapered.

In figs 11a and 11b, variants of the invention are shown which allow better possibilities of tailoring the capacitance of the device. in these versions of the invention, there There are still two conducting lines 1110, 1120, which are

located on either side of a ferroelectric layer supported by a non-conducting substrate, and the lines 1110, 1120, have sections which cross each other, preferably at an angle of 90 degrees, as was also the case in fig 7. However, in these variants, where the sections cross each other, one of the sections is 5 altered, to either have an aperture, preferably shaped as a square, or exhibits a significantly much narrower width during all or most of the crossing.

10 Figs 12a and 12b show top views of components in another example embodiment ~~1200-of the invention~~, and fig 12c shows the embodiment 1200 as a whole in a top view. This embodiment may give even further reduced losses and increased process tolerances, and uses a capacitance which reduces the required bias voltage, at the same time as it eliminates the floating ground in the middle.

15 Fig. 12a shows the bottom layer, and fig 12b shows the top layer, both layers being conducting, and separated in the same manner as the conductors in the embodiments shown in figs 7-10, 11a, and 11b.

20 The bottom conductor of Fig 12a and the top conductor of Fig 12b are of essentially the same design, and intended to be arranged “on top of each other”, with the mentioned separating layers between them, in such a manner that corresponding parts in each conductor “cover” each other. Each conductor comprises two meander shaped conducting patterns, being arranged to be each other’s mirror image with respect to an imaginary line

extending in the direction of the conductors, between saidthe conductors.

Thus, each of the meander patterns will have sections parallel to each other which extend perpendicularly to the general direction of extension of the conductor, and sections parallel to each other which have a direction of extension that coincides with the general direction of extension of the conductor, saidthe two kinds of sections alternating in the meander pattern.

Thus, in each meander line, of those sections which have a direction of extension that coincides with the general direction of extension of the conductor, there will be sections that are closest to the other meander line, and such sections which are the most distant from the other meander line.

In order to achieve the desired capacitive coupling, in the bottom conductor, every other such "closest" section comprises a protrusion towards the other meander line, the protrusion ending in a thin line, and every other closest section comprises a recess allowing for a slight "intrusion" of thesaid thin line.

In the top conductor, the "closest" sections corresponding to those closest sections in the bottom conductor which have thesaid recess comprise a square or rectangular aperture which will "enclose" thesaid intruding part of the thin line, although in an other plane of the device, thiswhich will enhance the production tolerance of the device.